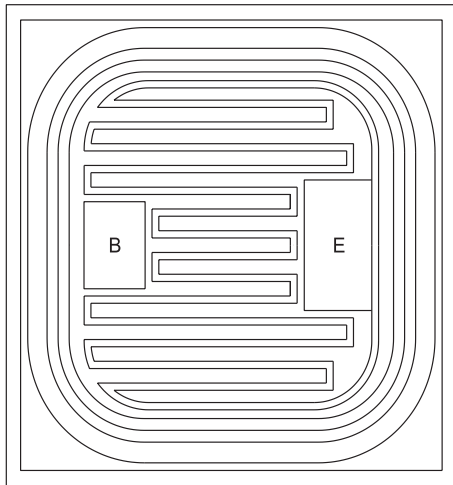


**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	63 x 63 MILS
Die Thickness	10 MILS
Base Bonding Pad Area	9 x 12 MILS
Emitter Bonding Pad Area	10 x 18 MILS
Top Side Metalization	Al - 16,000Å
Back Side Metalization	Au - 12,000Å

**GEOMETRY**



BACKSIDE COLLECTOR R0

**GROSS DIE PER 4 INCH WAFER**

2,840

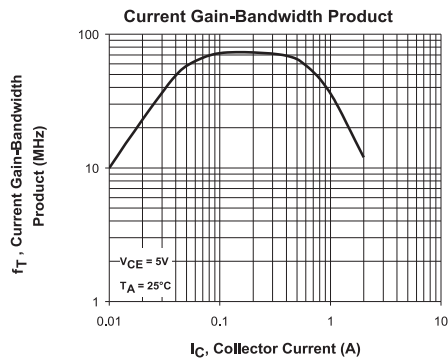
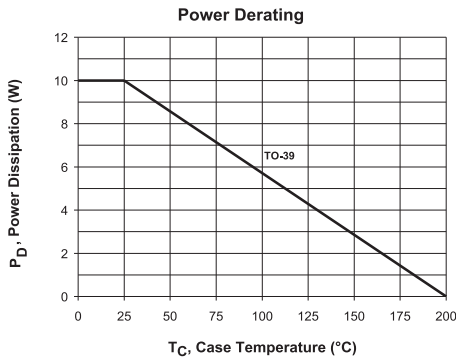
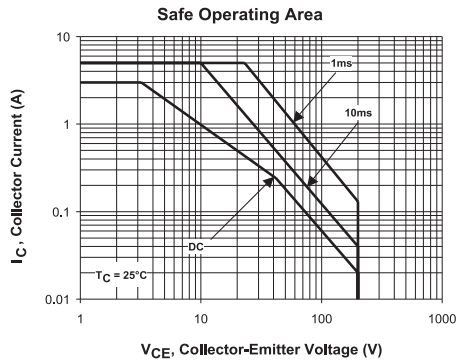
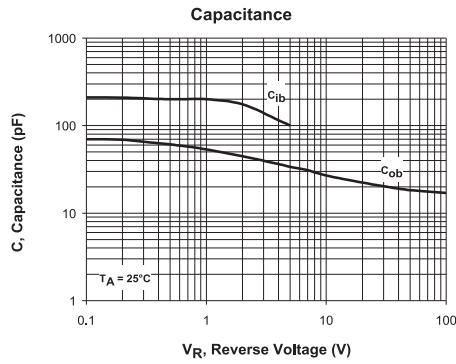
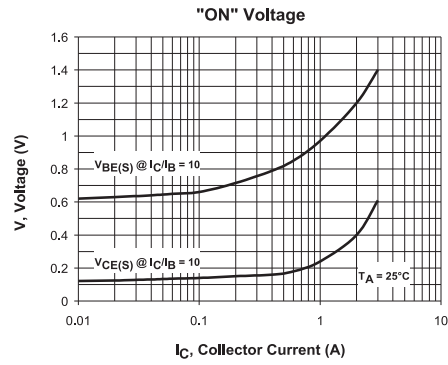
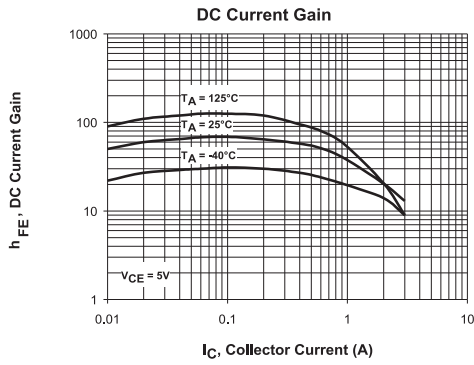
**PRINCIPAL DEVICE TYPES**

BUY49S

BSW68

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R1 (1-August 2002)



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